

R-C Thermal Model Parameters

DESCRIPTION

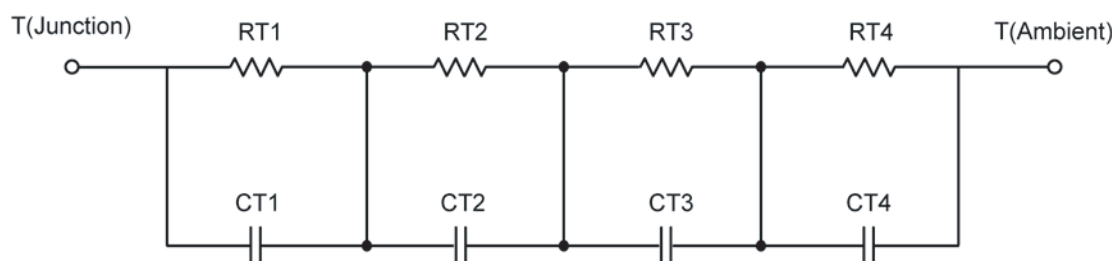
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

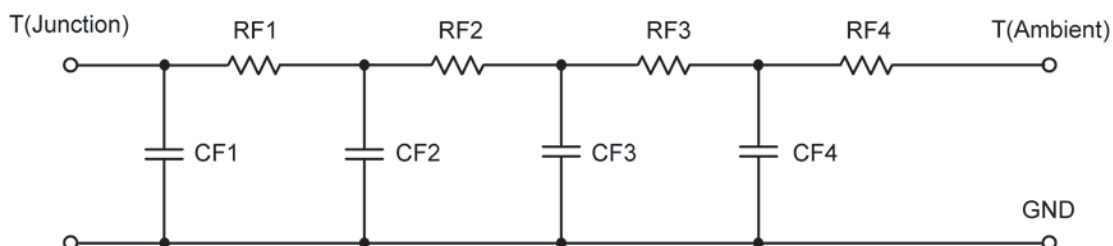
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|-----------------------------------|------------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | 1.7305 | 15.4007 m | N/A |
| RT2 | 11.6637 | 258.3547 m | N/A |
| RT3 | 8.7674 | 507.3918 m | N/A |
| RT4 | 42.3811 | 720.4557 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | 3.4792 m | 18.7014 μ | N/A |
| CT2 | 600.5512 m | 5.2493 m | N/A |
| CT3 | 58.3266 m | 77.4502 m | N/A |
| CT4 | 1.8962 | 51.9432 m | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION


| R-C VALUES FOR FILTER CONFIGURATION | | | |
|--|------------|----------------|------|
| Thermal Resistance ($^{\circ}\text{C}/\text{W}$) | | | |
| Junction to | Ambient | Case | Foot |
| RF1 | 2.9820 | 26.6223 m | N/A |
| RF2 | 8.4966 | 339.6323 m | N/A |
| RF3 | 16.5738 | 375.4330 m | N/A |
| RF4 | 36.6392 | 763.8146 m | N/A |
| Thermal Capacitance (Joules/ $^{\circ}\text{C}$) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | 7.7985 m | 959.7747 μ | N/A |
| CF2 | 39.7251 m | 3.6157 m | N/A |
| CF3 | 355.3409 m | 29.0619 m | N/A |
| CF4 | 1.7130 | 5.8830 μ | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

